

**3CG120,3CG130****PNP Silicon High Frequency Middle Power Transistor****Features:**

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit. Make up push pull amplifying circuit with NPN.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

**TECHNICAL DATA:****(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications					
			3CG120			3CG130		
			A	B	C	A	B	C
Total Dissipation	$P_{tot}$	mW	500 (Ta=25°C)			700 (Ta=25°C)		
Max. Collector Current	$I_{CM}$	mA	100			300		
Junction Temperature	$T_{jm}$	°C	175					
Storage Temperature	$T_{stg}$	°C	-55~+175					
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	15	30	45	15	30	45
			Ic=0.1mA					
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥4 (Ie=0.1 mA)					
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.5 (Ic=50mA, Ib=5mA)			0.5 (Ic=100mA, Ib=10mA)		
C-E Leakage Current	$I_{CEO}$	uA	1.0 (VCE=10V)					
DC Current Gain	$h_{FE}$		25~~270 (VCE=10V, Ic=30mA)			25~~270 (VCE=10V, Ic=50mA)		
Transition frequency	$f_T$	MHz	200			80		
			(VCE=10V, Ic=30mA, f=100MHz)			(VCE=10V, Ic=50mA, f=30MHz)		

**hFE Colored:**

Color	Orange	Yellow	Green	Blue	Purple	Gray
$h_{FE}$	25~40	40~55	55~80	80~120	120~180	180~270

**Outline and Dimensions:**